

MOS FIELD EFFECT TRANSISTOR μ PA2724T1A

SWITCHING N-CHANNEL POWER MOSFET

DESCRIPTION

The μ PA2724T1A is N-channel MOSFET designed for DC/DC converter applications.

FEATURES

• Low on-state resistance

 $R_{DS(on)1}$ = 3.3 m Ω MAX. (Vgs = 10 V, ID = 15 A)

 $R_{DS(on)2} = 5.0 \text{ m}\Omega \text{ MAX}. \text{ (VGS = 4.5 V, ID = 15 A)}$

· Low input capacitance

Ciss = 4400 pF TYP. (VDS = 15 V, VGS = 0 V)

- Built-in gate protection diode
- Thin type surface mount package with heat spreader (8-pin HVSON)
- RoHS Compliant

ABSOLUTE MAXIMUM RATINGS (TA = 25°C, All terminals are connected.)

Drain to Source Voltage (V _{GS} = 0 V)	VDSS	30	V	
Gate to Source Voltage (VDS = 0 V)	Vgss	±20	V	
Drain Current (DC)	ID(DC)	±29	Α	
Drain Current (pulse) Note1	ID(pulse)	±170	Α	
Total Power Dissipation Note2	P _{T1}	1.5	W	
Total Power Dissipation (PW = 10 sec) Note2	P _{T2}	4.6	W	
Channel Temperature	Tch	150	°C	
Storage Temperature	Tstg	-55 to +150	°C	
Single Avalanche Current Note3	las	29	Α	
Single Avalanche Energy Note3	Eas	84	mJ	

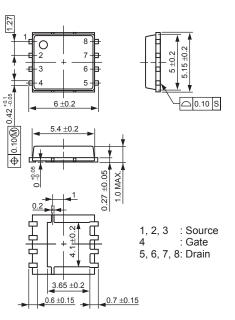
THERMAL RESISTANCE

Channel to Ambient Thermal Resistance Note2	Rth(ch-A)	83.3	°C/W
Channel to Case (Drain) Thermal Resistance	Rth(ch-C)	1.5	°C/W

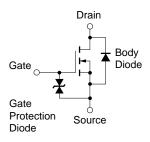
Notes 1. PW \leq 10 μ s, Duty Cycle \leq 1%

- 2. Mounted on a glass epoxy board of 25.4 mm x 25.4 mm x 0.8 mm $\,$
- 3. Starting T_{ch} = 25°C, V_{DD} = 15 V, R_G = 25 Ω , V_{GS} = 20 \rightarrow 0 V, L = 100 μ H

PACKAGE DRAWING (Unit: mm)



EQUIVALENT CIRCUIT



Remark The diode connected between the gate and source of the transistor serves as a protector against ESD. When this device actually used, an additional protection circuit is externally required if a voltage exceeding the rated voltage may be applied to this device.

The information in this document is subject to change without notice. Before using this document, please confirm that this is the latest version.

Not all products and/or types are available in every country. Please check with an NEC Electronics sales representative for availability and additional information.



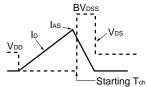
ELECTRICAL CHARACTERISTICS (TA = 25°C, All terminals are connected.)

CHARACTERISTICS	SYMBOL	TEST CONDITIONS	MIN.	TYP.	MAX.	UNIT
Zero Gate Voltage Drain Current	IDSS	V _{DS} = 30 V, V _{GS} = 0 V			10	μΑ
Gate Leakage Current	Igss	V _{GS} = ±20 V, V _{DS} = 0 V			±10	μΑ
Gate to Source Cut-off Voltage	V _{GS(off)}	V _{DS} = 10 V, I _D = 1 mA	1.5		2.5	٧
Forward Transfer Admittance Note	yfs	V _{DS} = 10 V, I _D = 15 A	13			S
Drain to Source On-state Resistance Note	RDS(on)1	V _{GS} = 10 V, I _D = 15 A		2.7	3.3	mΩ
	R _{DS(on)2}	V _{GS} = 4.5 V, I _D = 15 A		3.7	5.0	mΩ
Input Capacitance	Ciss	V _{DS} = 15 V,		4400		pF
Output Capacitance	Coss	V _{GS} = 0 V,		835		pF
Reverse Transfer Capacitance	Crss	f = 1 MHz		310		pF
Turn-on Delay Time	t _{d(on)}	V _{DD} = 15 V, I _D = 15 A,		26		ns
Rise Time	tr	V _{GS} = 10 V,		9.4		ns
Turn-off Delay Time	t _{d(off)}	R _G = 10 Ω		109		ns
Fall Time	t f			28		ns
Total Gate Charge	Q _G	V _{DD} = 15 V,		35		nC
Gate to Source Charge	QGS	V _{GS} = 5 V,		13		nC
Gate to Drain Charge	Q _{GD}	ID = 29 A		12		nC
Body Diode Forward Voltage Note	V _{F(S-D)}	I _F = 29 A, V _{GS} = 0 V		0.8		V
Reverse Recovery Time	trr	I _F = 29 A, V _{GS} = 0 V,		42		ns
Reverse Recovery Charge	Qrr	di/dt = 100 A/μs		43		nC
Gate Resistance	R _G	f = 1 MHz		1.8		Ω

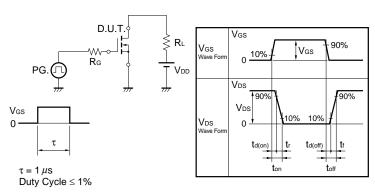
Note Pulsed

TEST CIRCUIT 1 AVALANCHE CAPABILITY

$V_{GS} = 20 \rightarrow 0 \text{ V}$ $PG. \bigcirc S = 20 \rightarrow 0 \text{ V}$ PRV_{GS} PV_{GS} PV_{GS}



TEST CIRCUIT 2 SWITCHING TIME

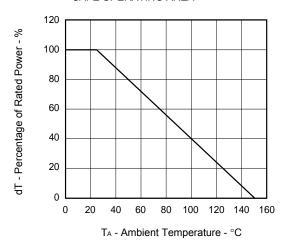


TEST CIRCUIT 3 GATE CHARGE

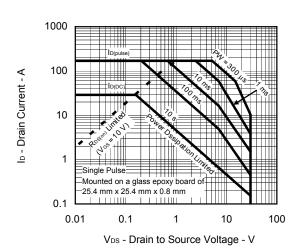
$$\begin{array}{c|c} D.U.T. \\ \hline \\ I_G = 2 \text{ mA} \\ \hline \\ \hline \\ \hline \\ \hline \\ \end{array} \begin{array}{c} R_L \\ \hline \\ \hline \\ V_{DD} \end{array}$$

TYPICAL CHARACTERISTICS (TA = 25°C)

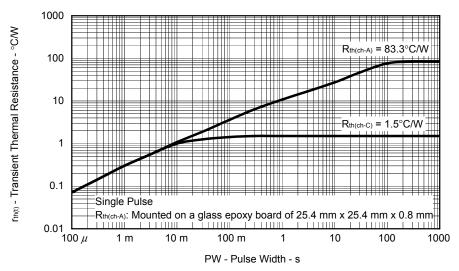
DERATING FACTOR OF FORWARD BIAS SAFE OPERATING AREA



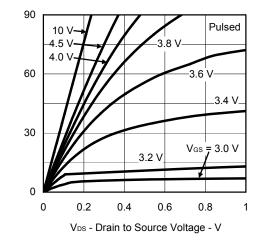
FORWARD BIAS SAFE OPERATING AREA



TRANSIENT THERMAL RESISTANCE vs. PULSE WIDTH

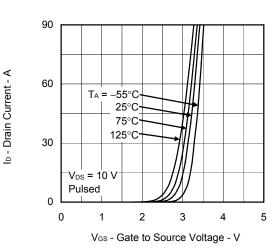


DRAIN CURRENT vs.
DRAIN TO SOURCE VOLTAGE

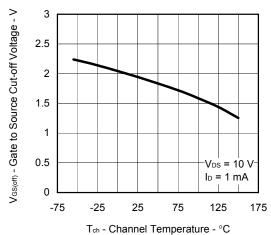


Ip - Drain Current - A

FORWARD TRANSFER CHARACTERISTICS

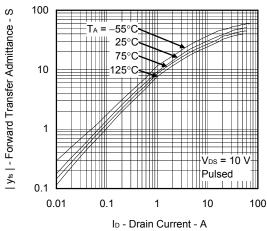


GATE TO SOURCE CUT-OFF VOLTAGE vs. CHANNEL TEMPERATURE

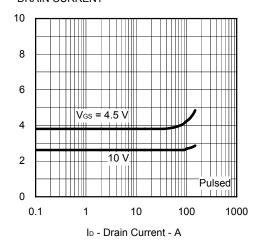


DRAIN CURRENT 100

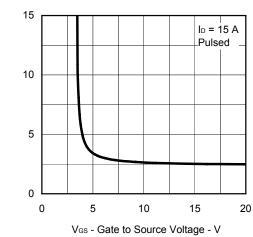
FORWARD TRANSFER ADMITTANCE vs.



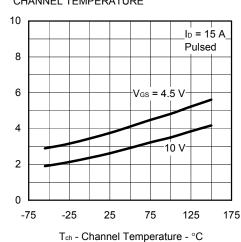
DRAIN TO SOURCE ON-STATE RESISTANCE vs. DRAIN CURRENT



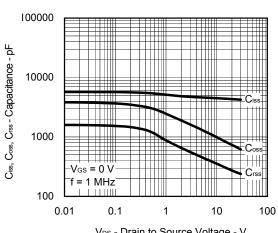
DRAIN TO SOURCE ON-STATE RESISTANCE vs. GATE TO SOURCE VOLTAGE



DRAIN TO SOURCE ON-STATE RESISTANCE vs. CHANNEL TEMPERATURE



CAPACITANCE vs. DRAIN TO SOURCE VOLTAGE



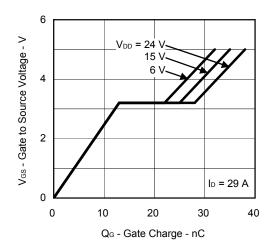
VDS - Drain to Source Voltage - V

R_{DS(on)} - Drain to Source On-state Resistance - mΩ

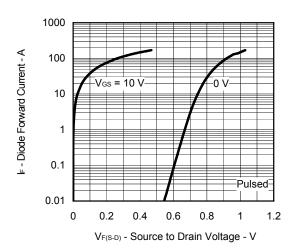
R_{DS(ση)} - Drain to Source On-state Resistance - mΩ

R_{DS(on)} - Drain to Source On-state Resistance - mΩ

DYNAMIC INPUT/OUTPUT CHARACTERISTICS



SOURCE TO DRAIN DIODE FORWARD VOLTAGE



ORDERING INFORMATION

PART NUMBER	LEAD PLATING	PACKING	PACKAGE	
μPA2724T1A-E1-AZ ^{Note}	C- D:			
μPA2724T1A-E2-AZ ^{Note}	Sn-Bi	Tana 2000 n/mal	8-pin HVSON	
μPA2724T1A-E1-AY Note	D 0	Tape 3000 p/reel	0.10 g TYP.	
μPA2724T1A-E2-AY Note	Pure Sn			

Note Pb-free (This product does not contain Pb in the external electrode.)

NEC μ PA2724T1A

The information in this document is current as of May, 2007. The information is subject to change
without notice. For actual design-in, refer to the latest publications of NEC Electronics data sheets or
data books, etc., for the most up-to-date specifications of NEC Electronics products. Not all
products and/or types are available in every country. Please check with an NEC Electronics sales
representative for availability and additional information.

- No part of this document may be copied or reproduced in any form or by any means without the prior written consent of NEC Electronics. NEC Electronics assumes no responsibility for any errors that may appear in this document.
- NEC Electronics does not assume any liability for infringement of patents, copyrights or other intellectual property rights of third parties by or arising from the use of NEC Electronics products listed in this document or any other liability arising from the use of such products. No license, express, implied or otherwise, is granted under any patents, copyrights or other intellectual property rights of NEC Electronics or others.
- Descriptions of circuits, software and other related information in this document are provided for illustrative
 purposes in semiconductor product operation and application examples. The incorporation of these
 circuits, software and information in the design of a customer's equipment shall be done under the full
 responsibility of the customer. NEC Electronics assumes no responsibility for any losses incurred by
 customers or third parties arising from the use of these circuits, software and information.
- While NEC Electronics endeavors to enhance the quality, reliability and safety of NEC Electronics products, customers agree and acknowledge that the possibility of defects thereof cannot be eliminated entirely. To minimize risks of damage to property or injury (including death) to persons arising from defects in NEC Electronics products, customers must incorporate sufficient safety measures in their design, such as redundancy, fire-containment and anti-failure features.
- NEC Electronics products are classified into the following three quality grades: "Standard", "Special" and "Specific".
 - The "Specific" quality grade applies only to NEC Electronics products developed based on a customerdesignated "quality assurance program" for a specific application. The recommended applications of an NEC Electronics product depend on its quality grade, as indicated below. Customers must check the quality grade of each NEC Electronics product before using it in a particular application.
 - "Standard": Computers, office equipment, communications equipment, test and measurement equipment, audio and visual equipment, home electronic appliances, machine tools, personal electronic equipment and industrial robots.
 - "Special": Transportation equipment (automobiles, trains, ships, etc.), traffic control systems, anti-disaster systems, anti-crime systems, safety equipment and medical equipment (not specifically designed for life support).
 - "Specific": Aircraft, aerospace equipment, submersible repeaters, nuclear reactor control systems, life support systems and medical equipment for life support, etc.

The quality grade of NEC Electronics products is "Standard" unless otherwise expressly specified in NEC Electronics data sheets or data books, etc. If customers wish to use NEC Electronics products in applications not intended by NEC Electronics, they must contact an NEC Electronics sales representative in advance to determine NEC Electronics' willingness to support a given application.

(Note)

- (1) "NEC Electronics" as used in this statement means NEC Electronics Corporation and also includes its majority-owned subsidiaries.
- (2) "NEC Electronics products" means any product developed or manufactured by or for NEC Electronics (as defined above).